



# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors





# BTA425X-800B

3Q Hi-Com Triac

17 July 2014

Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package intended for use in circuits where high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. This "series B" triac will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- High immunity to false turn-on by  $dV/dt$
- High minimum IGT for guaranteed immunity to gate noise
- High voltage capability
- Isolated mounting base package
- Least sensitive gate for highest noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very high commutation capability with maximum false trigger immunity

## 3. Applications

- Electronic thermostats
- Heating control
- High power motor control
- High power switching

## 4. Quick reference data

Table 1. Quick reference data

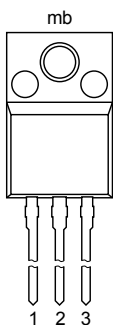
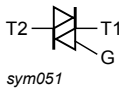
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	250	A
$I_{T(\text{RMS})}$	RMS on-state current	full sine wave; $T_n \leq 38\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	25	A
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; Fig. 7	-	-	50	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	2000	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 25\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit	15	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 <p>TO-220F (SOT186A)</p>	 <p>sym051</p>
2	T2	main terminal 2		
3	G	gate		
mb	n.c.	mounting base; isolated		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA425X-800B	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A

## 7. Marking

Table 4. Marking codes

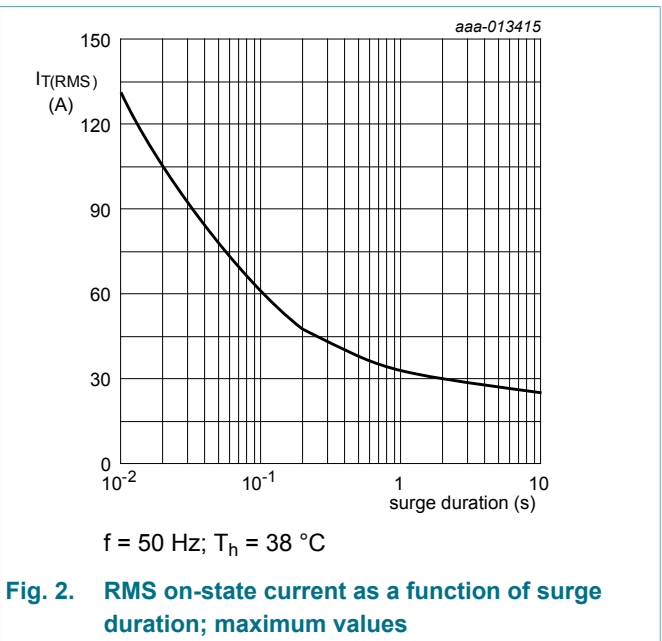
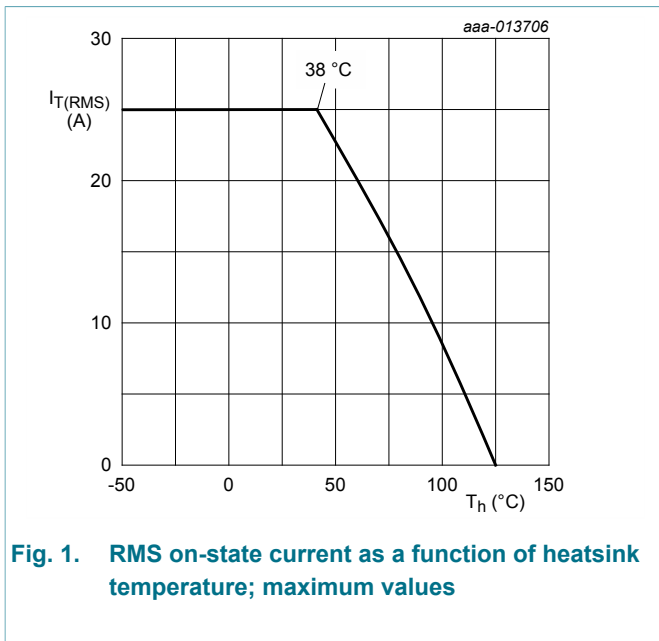
Type number	Marking code
BTA425X-800B	BTA425X-800B

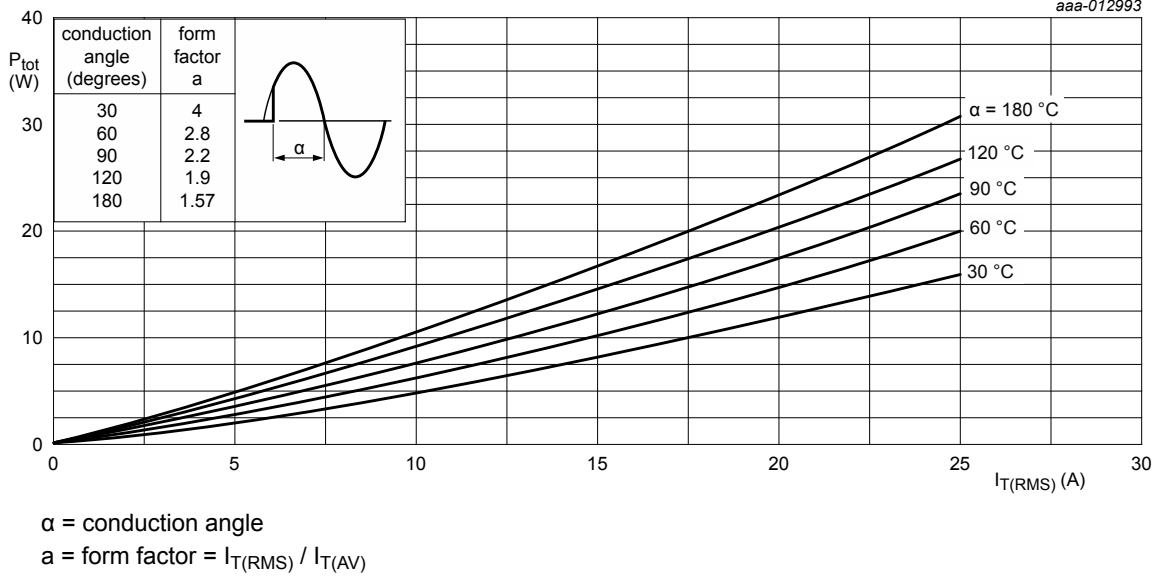
## 8. Limiting values

**Table 5. Limiting values**

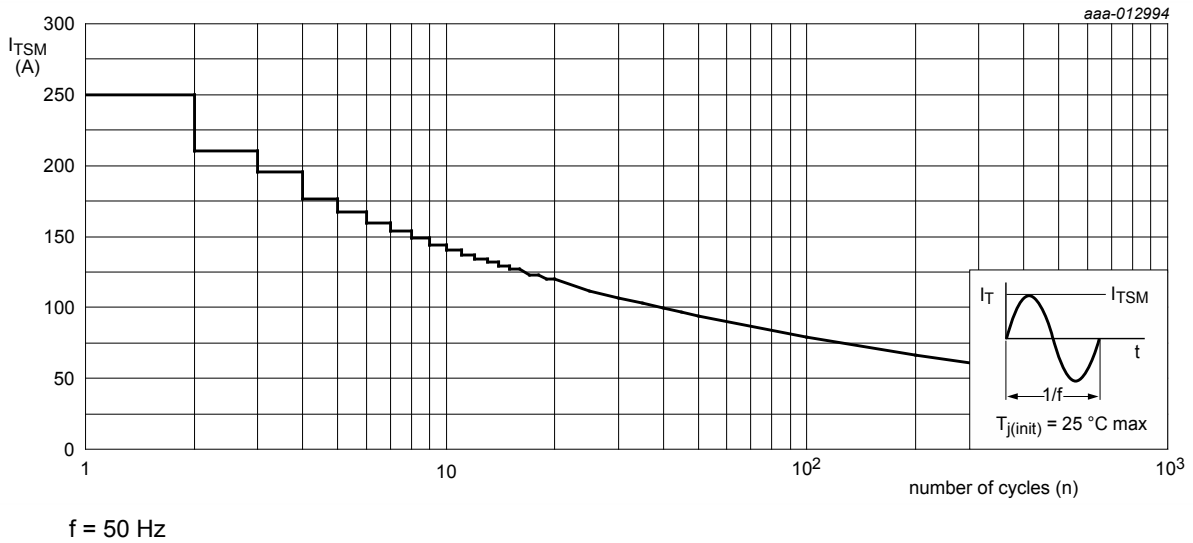
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_h \leq 38\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	25	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	250	A
		full sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 16.7\text{ ms}$	-	275	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	312.5	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_T = 30\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $di_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	$^\circ\text{C}$
$T_j$	junction temperature		-	125	$^\circ\text{C}$

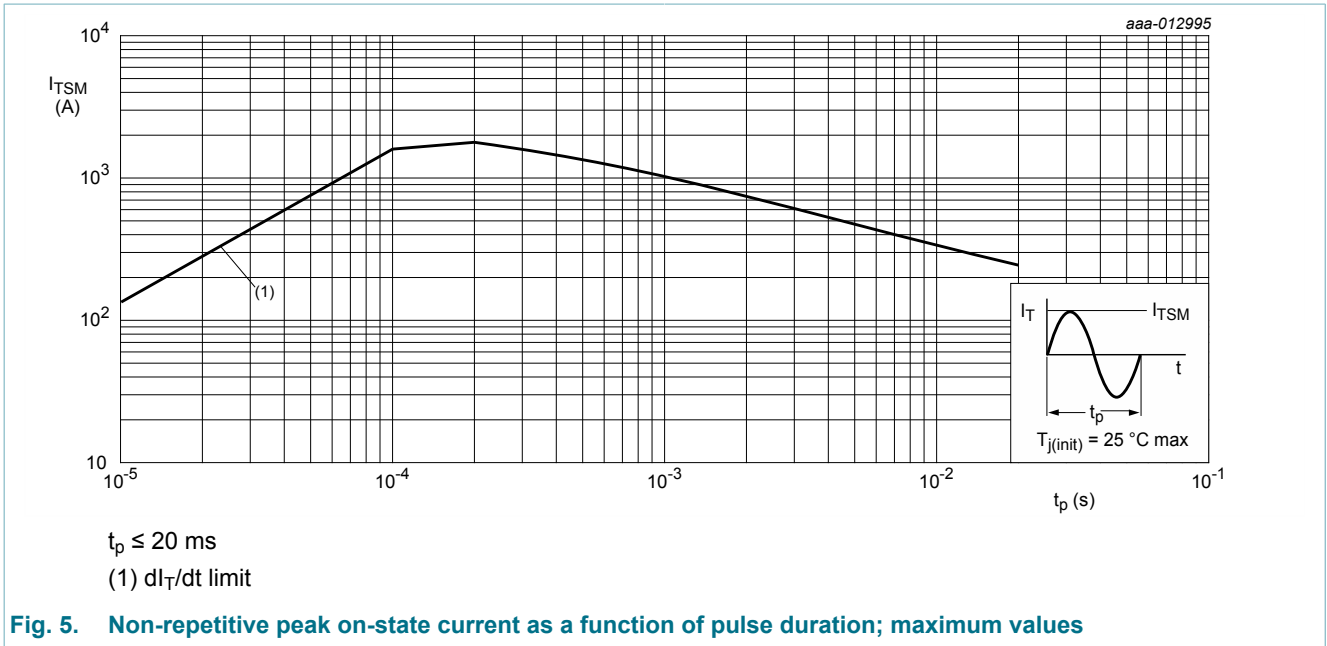




**Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values**



**Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values**



## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full cycle ; with heatsink compound; <a href="#">Fig. 6</a>	-	-	2.8	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W

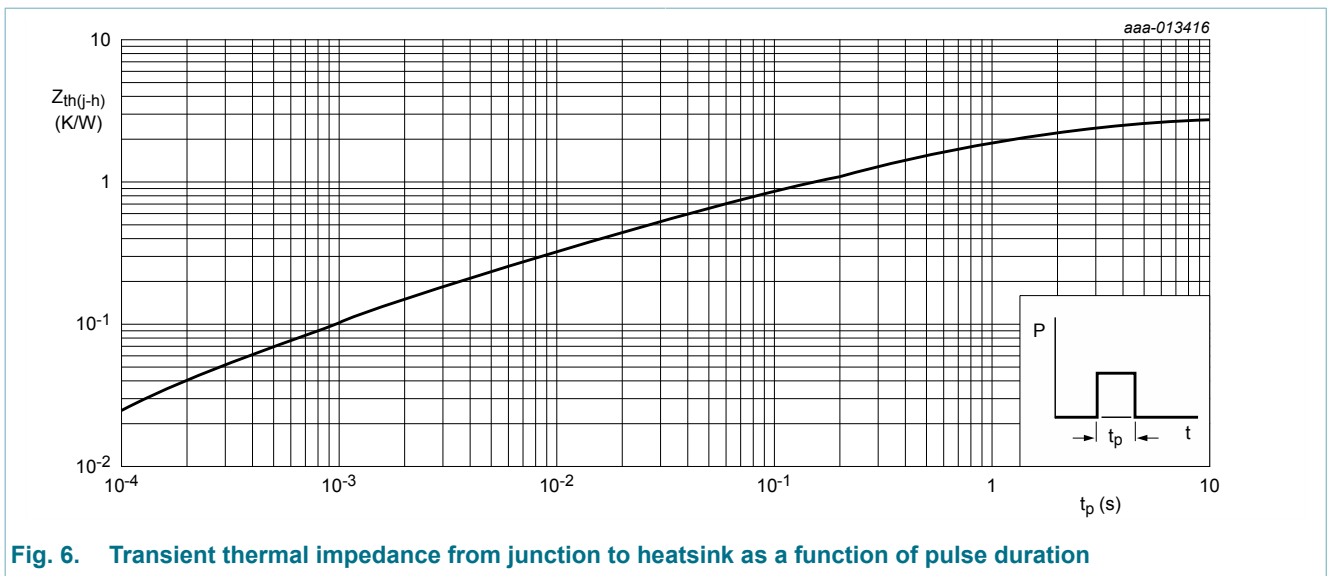


Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

## 10. Isolation characteristics

Table 7. Isolation characteristics

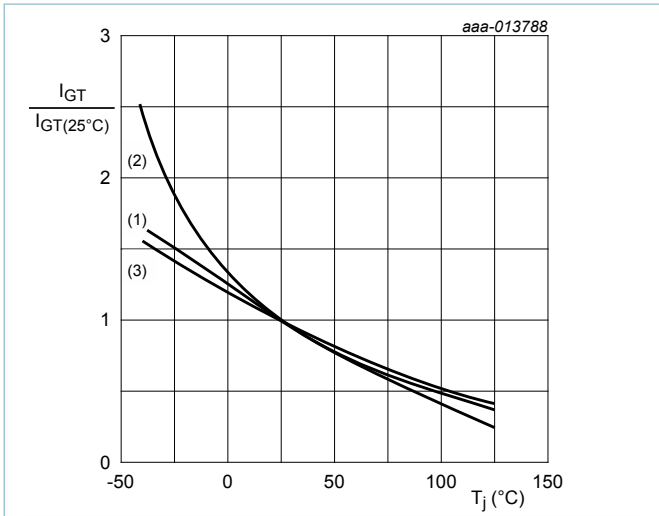
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$ ; $RH \leq 65\%$ ; $T_h = 25\text{ }^\circ\text{C}$	-	-	2500	V
$C_{isol}$	isolation capacitance	from main terminal 2 to external heatsink; $f = 1\text{ MHz}$ ; $T_h = 25\text{ }^\circ\text{C}$	-	10	-	pF

## 11. Characteristics

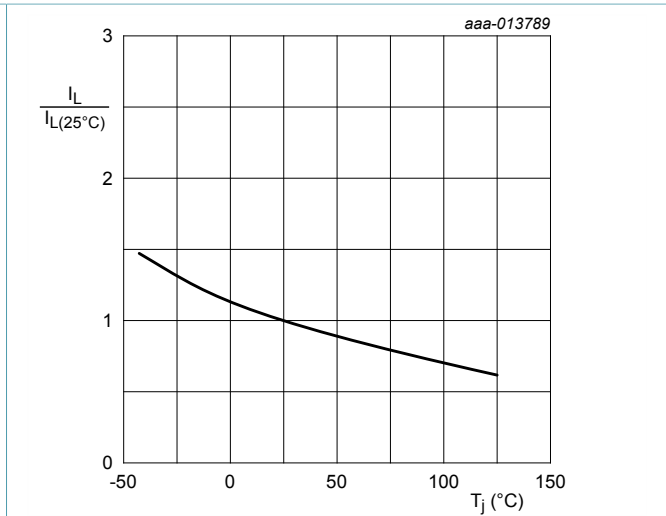
Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>	-	-	50	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	-	-	80	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	-	-	100	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>	-	-	80	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	-	75	mA
$V_T$	on-state voltage	$I_T = 35\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	0.9	1.3	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	0.2	0.45	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$	-	0.4	2	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	2000	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 25\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit	15	-	-	A/ms

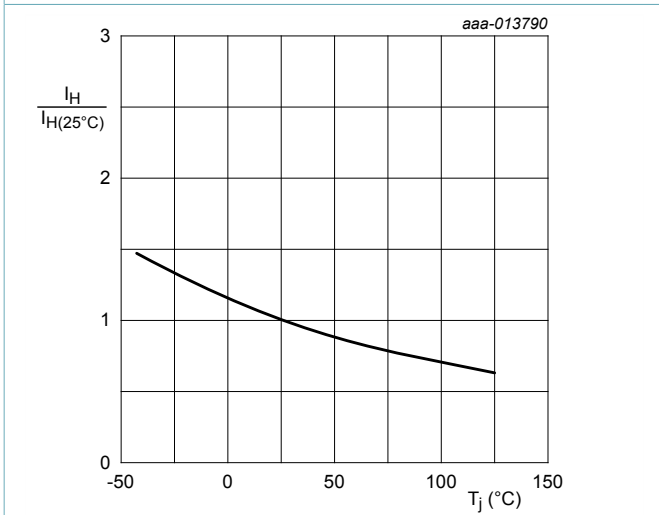




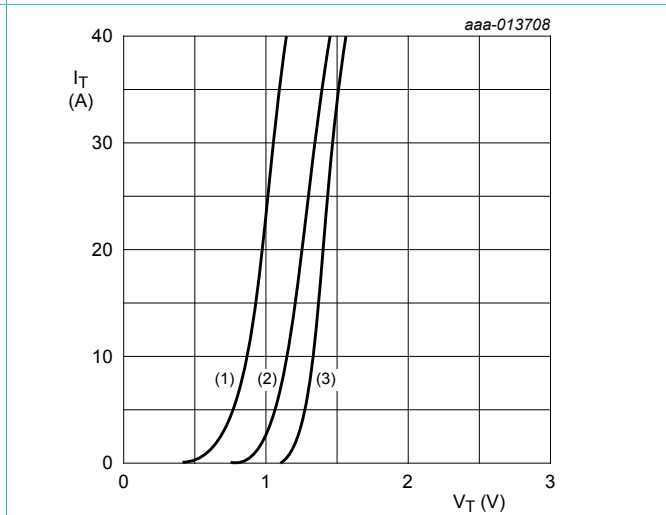
**Fig. 7. Normalized gate trigger current as a function of junction temperature**



**Fig. 8. Normalized latching current as a function of junction temperature**



**Fig. 9. Normalized holding current as a function of junction temperature**



$V_o = 1.085 \text{ V}; R_s = 0.011 \Omega$

(1)  $T_j = 125 \text{ }^\circ\text{C}$ ; typical values

(2)  $T_j = 125 \text{ }^\circ\text{C}$ ; maximum values

(3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

**Fig. 10. On-state current as a function of on-state voltage**

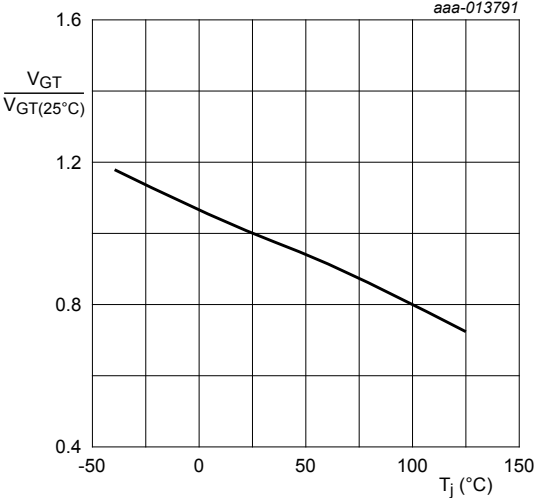


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

## 12. Package outline



Fig. 12. Package outline TO-220F (SOT186A)

## 13. Legal information

### 13.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## 14. Contents

1	General description .....	1
2	Features and benefits .....	1
3	Applications .....	1
4	Quick reference data .....	1
5	Pinning information .....	2
6	Ordering information .....	2
7	Marking .....	2
8	Limiting values .....	3
9	Thermal characteristics .....	6
10	Isolation characteristics .....	6
11	Characteristics .....	7
12	Package outline .....	10
13	Legal information .....	11
13.1	Data sheet status .....	11
13.2	Definitions .....	11
13.3	Disclaimers .....	11
13.4	Trademarks .....	12

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